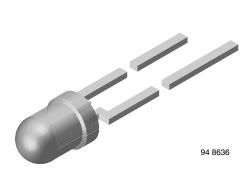


Vishay Semiconductors

Infrared Emitting Diode, RoHS Compliant, 875 nm, GaAlAs



DESCRIPTION

The TSHA440. series are infrared, 875 nm emitting diodes in GaAlAs technology, molded in a clear, untinted plastic package.

FEATURES

Package type: leadedPackage form: T-1

Dimensions (in mm): Ø 3
 Peak wavelength: λ_p = 875 nm

· High reliability

• Angle of half intensity: $\varphi = \pm 20^{\circ}$

· Low forward voltage

• Suitable for high pulse current operation

Good spectral matching with Si photodetectors

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



- Infrared remote control and free air data transmission systems with comfortable radiation angle
- This emitter series is dedicated to systems with panes in transmission space between emitter and detector, because of the low absorbtion of 875 nm radiation in glass

PRODUCT SUMMARY					
COMPONENT	l _e (mW/sr)	φ (deg)	λ _P (nm)	t _r (ns)	
TSHA4400	20	± 20	875	600	
TSHA4401	30	± 20	875	600	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION						
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM			
TSHA4400	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1			
TSHA4401	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1			

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
Reverse voltage		V_{R}	5	V		
Forward current		I _F	100	mA		
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I _{FM}	200	mA		
Surge forward current	t _p = 100 μs	I _{FSM}	2	Α		
Power dissipation		P _V	180	mW		
Junction temperature		Tj	100	°C		
Operating temperature range		T _{amb}	- 40 to + 85	°C		
Storage temperature range		T _{stg}	- 40 to + 100	°C		
Soldering temperature	$t \le 5$ s, 2 mm from case	T _{sd}	260	°C		
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R _{thJA}	300	K/W		

Note

T_{amb} = 25 °C, unless otherwise specified

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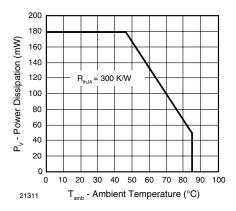


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	CONDITION SYMBOL		TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V _F		1.5	1.8	V
	$I_F = 1.5 \text{ A}, t_p = 100 \mu\text{s}$	V _F		3.2	4.9	V
Temperature coefficient of V _F	I _F = 100 mA	TK _{VF}		- 1.6		mV/K
Reverse current	V _R = 5 V	I _R			100	μΑ
Junction capacitance	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	Cj		20		pF
Temperature coefficient of φ _e	I _F = 100 mA	TKφe		- 0.7		%/K
Angle of half intensity		φ		± 20		deg
Peak wavelength	I _F = 100 mA	λ_{p}		875		nm
Spectral bandwidth	I _F = 100 mA	Δλ		80		nm
Temperature coefficient of λ_p	I _F = 100 mA	TKλ _p		0.2		nm/K
B:	I _F = 100 mA	t _r		600		ns
Rise time	I _F = 1.5 A	t _r		300		ns
Fall time	I _F = 100 mA	t _f		600		ns
Fall time	I _F = 1.5 A	t _f		300		ns
Virtual source diameter		d		1.8		mm

Note

 T_{amb} = 25 °C, unless otherwise specified

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Radiant intensity	L = 100 mA + = 20 mg	TSHA4400	l _e	12	20	60	mW/sr
	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	TSHA4401	l _e	16	30	60	mW/sr
	L = 1.5 mA + = 100 up	TSHA4400	l _e	140	240		mW/sr
	$I_F = 1.5 \text{ mA}, t_p = 100 \mu s$	TSHA4401	l _e	190	360		mW/sr
Radiant power	L = 100 mA + = 20 mg	TSHA4400	фе		20		mW
	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	TSHA4401	фe		24		mW

Note

T_{amb} = 25 °C, unless otherwise specified



Infrared Emitting Diode, RoHS Compliant, Vishay Semiconductors 875 nm, GaAlAs

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

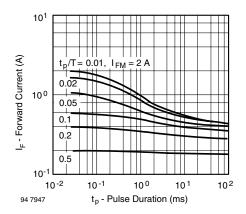


Fig. 3 - Pulse Forward Current vs. Pulse Duration

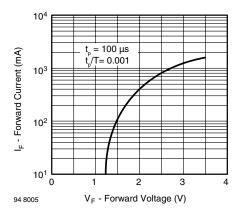


Fig. 4 - Forward Current vs. Forward Voltage

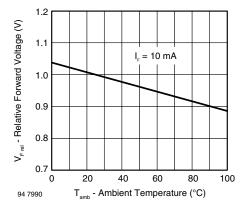


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

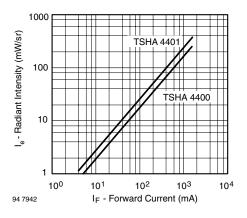


Fig. 6 - Radiant Intensity vs. Forward Current

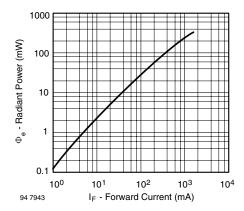


Fig. 7 - Radiant Power vs. Forward Current

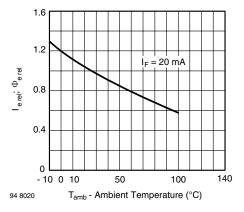


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

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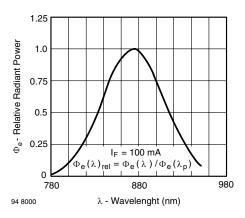


Fig. 9 - Relative Radiant Power vs. Wavelength

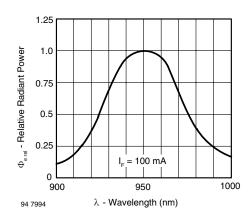
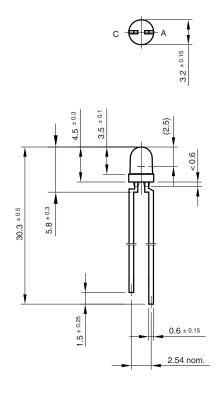


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



Area not plane
2.9 ± 0.1

0.4 + 0.15
-0.05



specifications

Drawing-No.: 6.544-5264.01-4

Issue: 2; 23.04.98

95 10951





Vishay

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